temperature. To understand the mechanism of hydrogen release by applying current flow during annealing, the change in current values p-type GaN contacts during annealing has been observed. By using regression analysis and kinetic model, the electrical conduction improvement achieved by applying current flow through GaN substrate during annealing have been analysis. The results suggest that by applying current flow during annealing and by forming a contact with material that H can diffuse into such as Pd, the H release from GaN substrate can be enhanced and the electrical conduction of p-type GaN contact can be significantly improved.

References:


Achievement:

Chapter 4


Chapter 5


Chapter 6

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